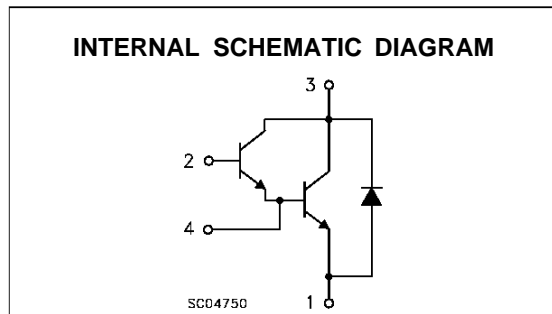
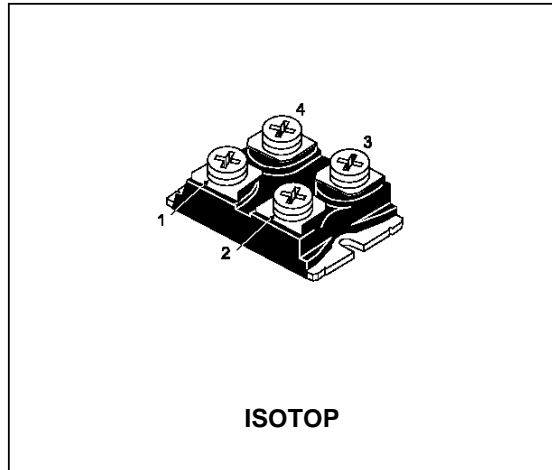


NPN DARLINGTON POWER MODULE

- HIGH CURRENT POWER BIPOLAR MODULE
- VERY LOW R_{th} JUNCTION CASE
- SPECIFIED ACCIDENTAL OVERLOAD AREAS
- ULTRAFAST FREEWHEELING DIODE
- ISOLATED CASE (2500V RMS)
- EASY TO MOUNT
- LOW INTERNAL PARASITIC INDUCTANCE

INDUSTRIAL APPLICATIONS:

- MOTOR CONTROL
- UPS
- DC/DC & DC/AC CONVERTERS



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|----------------|--|------------|------|
| V_{CEV} | Collector-Emitter Voltage ($V_{BE} = -5$ V) | 400 | V |
| $V_{CEO(sus)}$ | Collector-Emitter Voltage ($I_B = 0$) | 300 | V |
| V_{EBO} | Emitter-Base Voltage ($I_C = 0$) | 7 | V |
| I_C | Collector Current | 67 | A |
| I_{CM} | Collector Peak Current ($t_p = 10$ ms) | 100 | A |
| I_B | Base Current | 3 | A |
| I_{BM} | Base Peak Current ($t_p = 10$ ms) | 6 | A |
| P_{tot} | Total Dissipation at $T_c = 25$ °C | 150 | W |
| T_{stg} | Storage Temperature | -55 to 150 | °C |
| T_j | Max. Operating Junction Temperature | 150 | °C |
| V_{ISO} | Insulation Withstand Voltage (AC-RMS) | 2500 | °C |

ESM2030DV

THERMAL DATA

| | | | | |
|-----------------------|---|-----|------|------|
| R _{thj-case} | Thermal Resistance Junction-case (transistor) | Max | 0.83 | °C/W |
| R _{thj-case} | Thermal Resistance Junction-case (diode) | Max | 1.2 | °C/W |
| R _{thc-h} | Thermal Resistance Case-heatsink With Conductive Grease Applied | Max | 0.05 | °C/W |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------|---|--|------|---------------------------|------------|------------------|
| I _{CER} # | Collector Cut-off Current (R _{BE} = 5 Ω) | V _{CE} = V _{CEV} V _{CE} = V _{CEV} T _j = 100 °C | | | 1.5 16 | mA mA |
| I _{CEV} # | Collector Cut-off Current (V _{BE} = -5V) | V _{CE} = V _{CEV} V _{CE} = V _{CEV} T _j = 100 °C | | | 1 11 | mA mA |
| I _{EBO} # | Emitter Cut-off Current (I _C = 0) | V _{EB} = 5 V | | | 1 | mA |
| V _{CEO(SUS)} * | Collector-Emitter Sustaining Voltage | I _C = 0.2 A L = 25 mH V _{clamp} = 300 V | 300 | | | V |
| h _{FE} * | DC Current Gain | I _C = 56 A V _{CE} = 5 V | | 300 | | |
| V _{CE(sat)} * | Collector-Emitter Saturation Voltage | I _C = 40 A I _B = 0.4 A I _C = 40 A I _B = 0.4 A T _j = 100 °C I _C = 56 A I _B = 1.6 A I _C = 56 A I _B = 1.6 A T _j = 100 °C | | 1.25 1.4 1.5 1.8 | 1.8 2.2 | V V V V |
| V _{BE(sat)} * | Base-Emitter Saturation Voltage | I _C = 56 A I _B = 1.6 A I _C = 56 A I _B = 1.6 A T _j = 100 °C | | 2.4 2.5 | 3 | V V |
| di _C /dt | Rate of Rise of On-state Collector | V _{CC} = 300 V R _C = 0 t _p = 3 μs I _{B1} = 0.6 A T _j = 100 °C | 220 | 260 | | A/μs |
| V _{CE(3 μs)} • | Collector-Emitter Dynamic Voltage | V _{CC} = 300 V R _C = 7.5 Ω I _{B1} = 0.6 A T _j = 100 °C | | 3 | 6 | V |
| V _{CE(5 μs)} • | Collector-Emitter Dynamic Voltage | V _{CC} = 300 V R _C = 7.5 Ω I _{B1} = 0.6 A T _j = 100 °C | | 2.2 | 4 | V |
| t _s | Storage Time | I _C = 40 A V _{CC} = 50 V | | 2 | 3 | μs |
| t _f | Fall Time | V _{BB} = -5 V R _{BB} = 0.6 Ω | | 0.35 | 0.6 | μs |
| t _c | Cross-over Time | V _{clamp} = 300 V I _{B1} = 0.4 A L = 0.06 mH T _j = 100 °C | | 0.8 | 1.2 | μs |
| V _{CEW} | Maximum Collector Emitter Voltage Without Snubber | I _{CWoff} = 67 A I _{B1} = 1.6 A V _{BB} = -5 V V _{CC} = 50 V L = 0.037 mH R _{BB} = 0.6 Ω T _j = 125 °C | 300 | | | V |
| V _F * | Diode Forward Voltage | I _F = 56 A T _j = 100 °C | | 1.15 | 1.6 | V |
| I _{RM} | Reverse Recovery Current | V _{CC} = 200 V I _F = 56 A di _F /dt = -220 A/μs L < 0.05 μH T _j = 100 °C | | 12 | 17 | A |

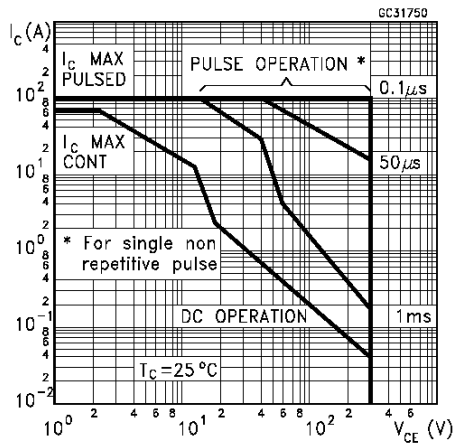
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

See test circuit in databook introduction

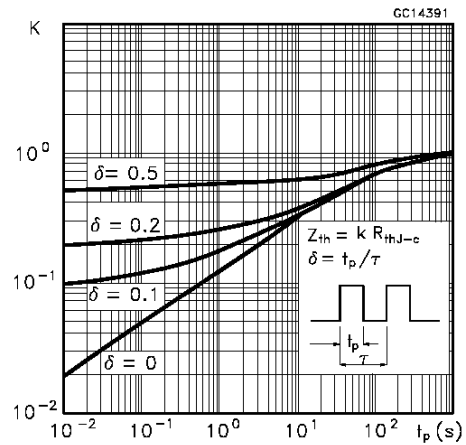
To evaluate the conduction losses of the diode use the following equations:

$$V_F = 1.1 + 0.0045 I_F \quad P = 1.1 I_{F(AV)} + 0.0045 I_{F(RMS)}^2$$

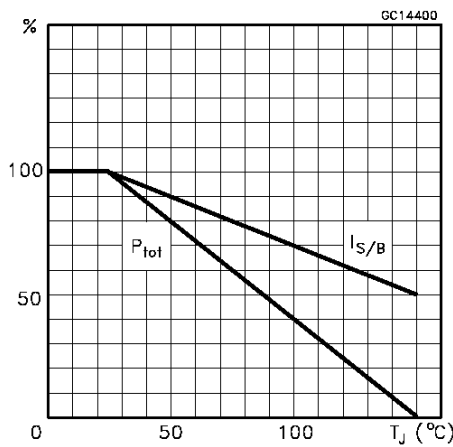
Safe Operating Areas



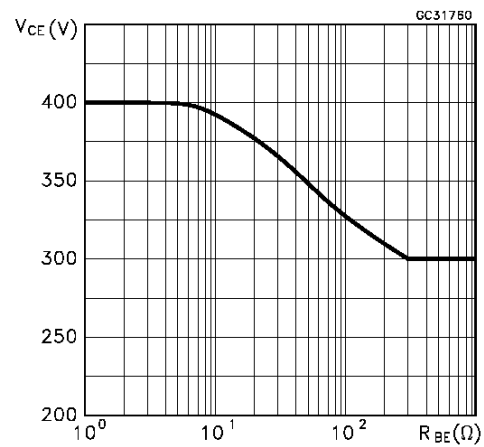
Thermal Impedance



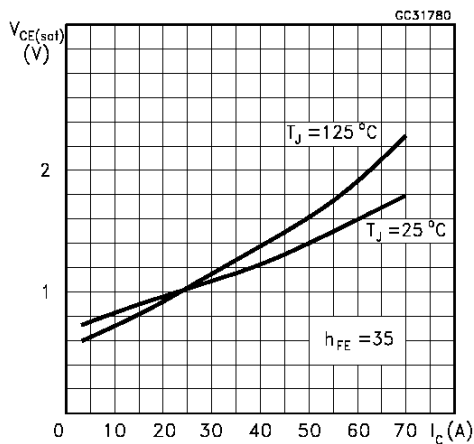
Derating Curve



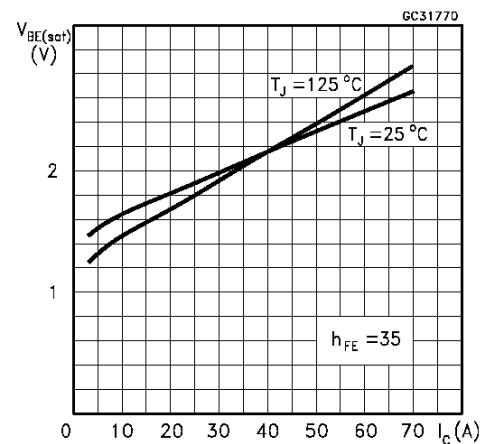
Collector-emitter Voltage Versus base-emitter Resistance



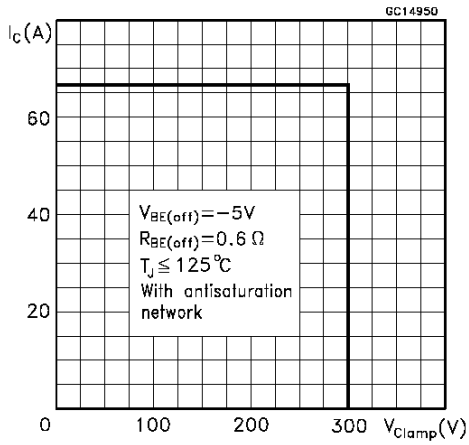
Collector Emitter Saturation Voltage



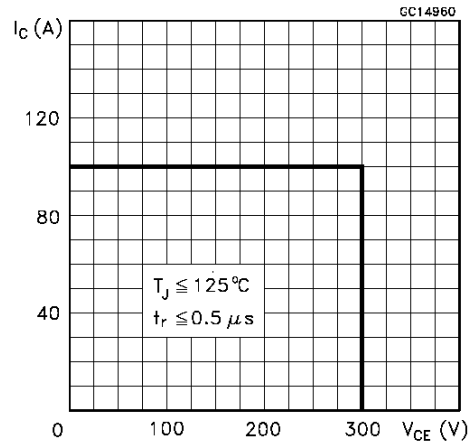
Base-Emitter Saturation Voltage



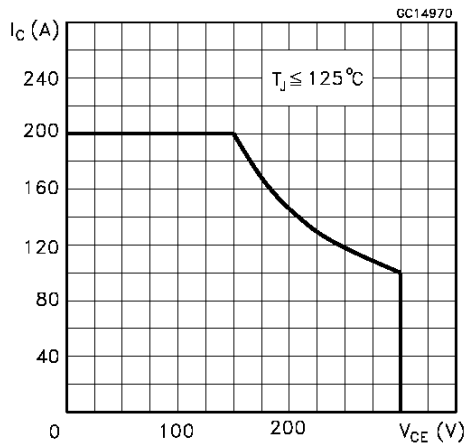
Reverse Biased SOA



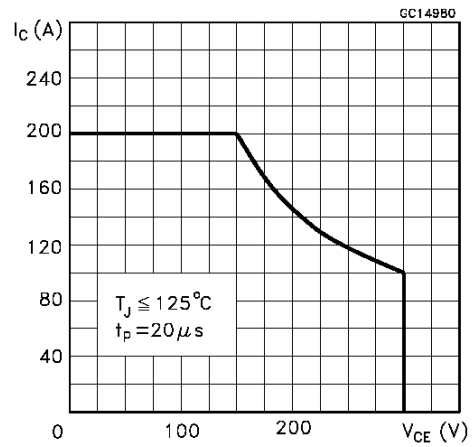
Foward Biased SOA



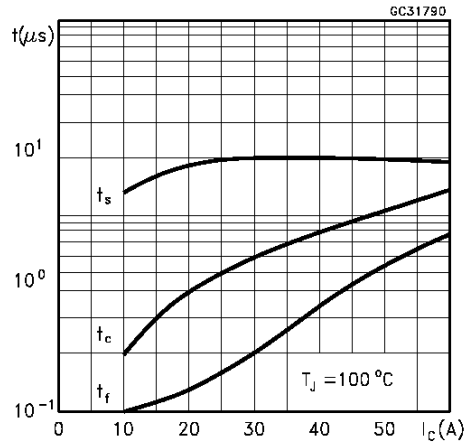
Reverse Biased AOA



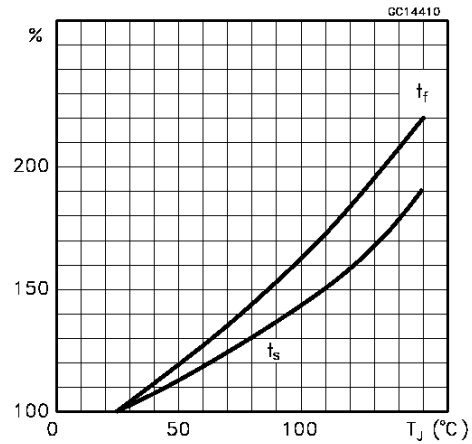
Forward Biased AOA



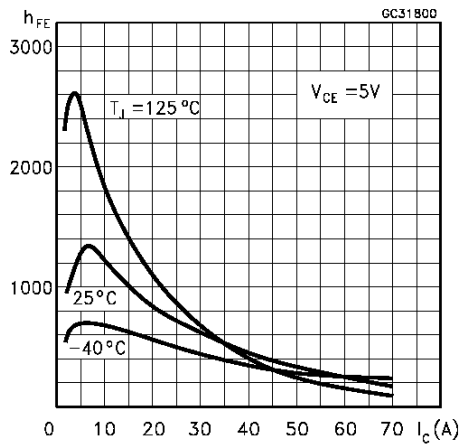
Switching Times Inductive Load



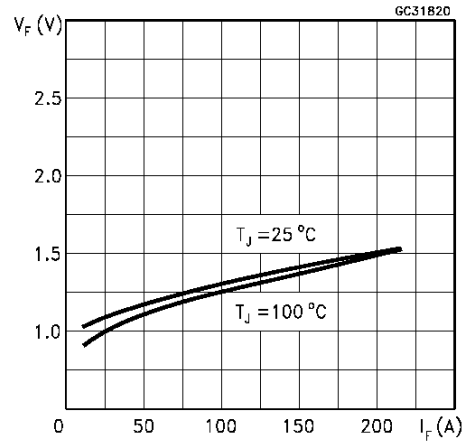
Switching Times Inductive Load Versus Temperature



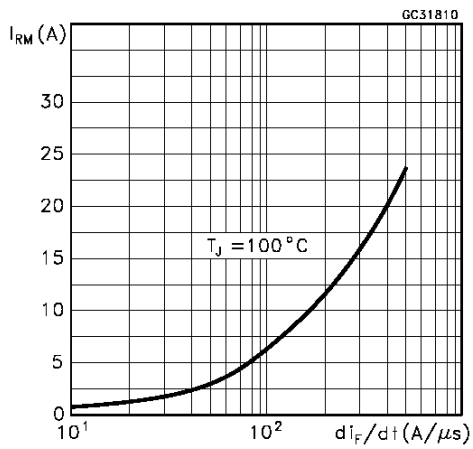
Dc Current Gain



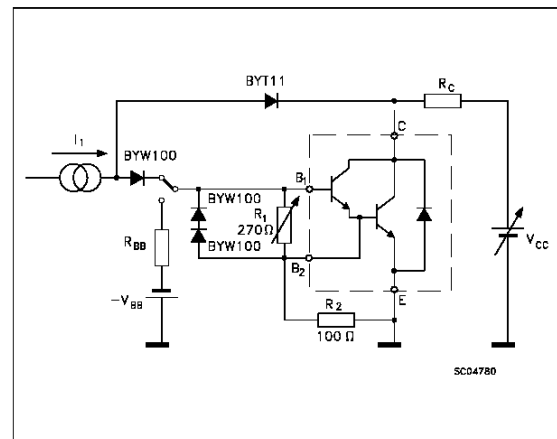
Typical VF Versus IF



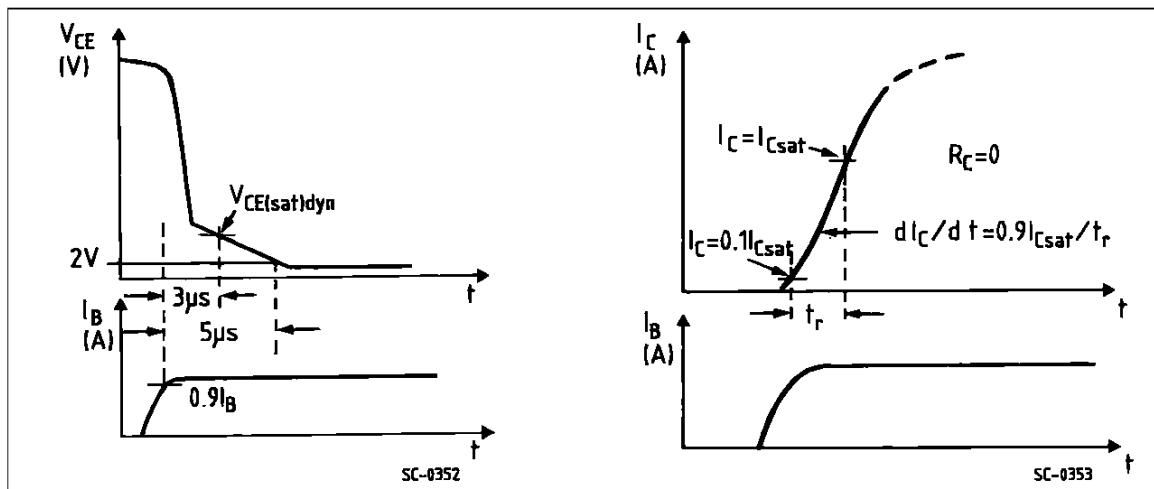
Peak Reverse Current Versus diF/dt



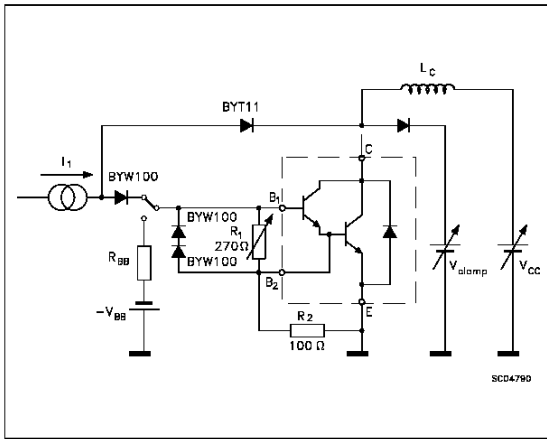
Turn-on Switching Test Circuit



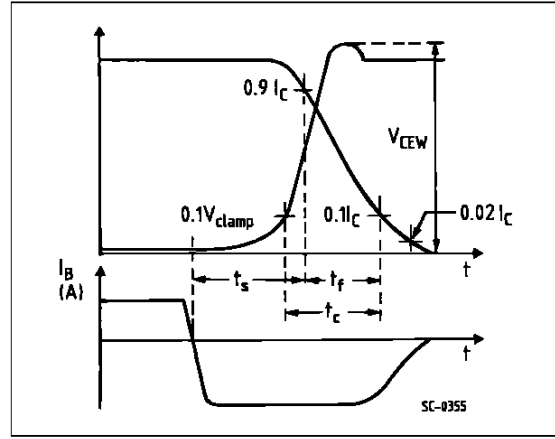
Turn-on Switching Waveforms



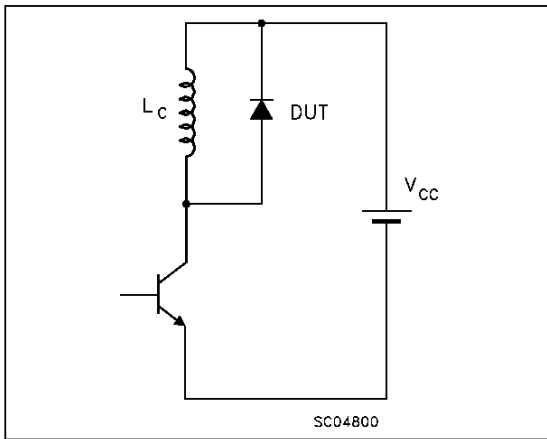
Turn-on Switching Test Circuit



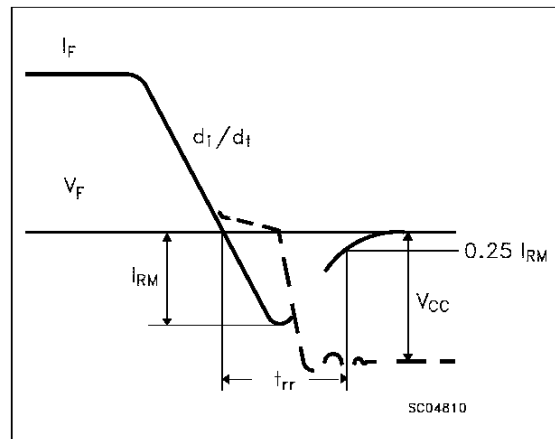
Turn-off Switching Waveforms



Turn-off Switching Test Circuit of Diode

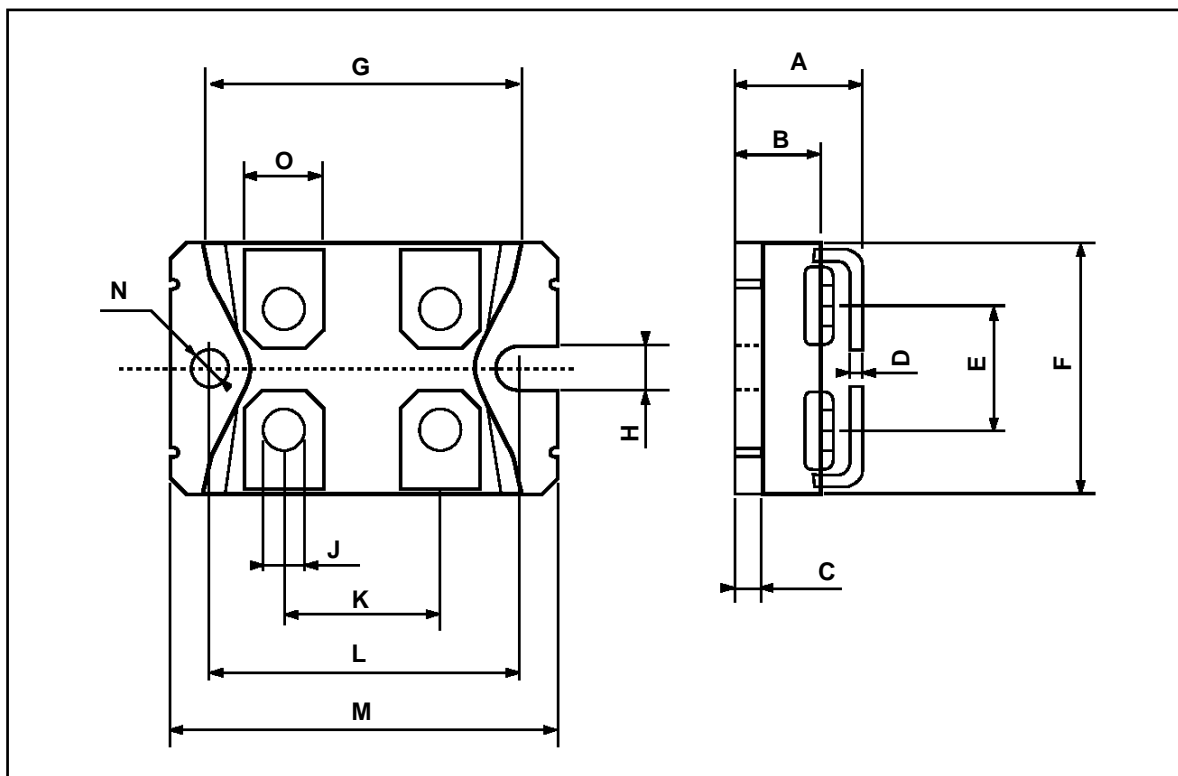


Turn-off Switching Waveform of Diode



ISOTOP MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-------|------|------|-------|------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 11.8 | | 12.2 | 0.466 | | 0.480 |
| B | 8.9 | | 9.1 | 0.350 | | 0.358 |
| C | 1.95 | | 2.05 | 0.076 | | 0.080 |
| D | 0.75 | | 0.85 | 0.029 | | 0.033 |
| E | 12.6 | | 12.8 | 0.496 | | 0.503 |
| F | 25.15 | | 25.5 | 0.990 | | 1.003 |
| G | 31.5 | | 31.7 | 1.240 | | 1.248 |
| H | 4 | | | 0.157 | | |
| J | 4.1 | | 4.3 | 0.161 | | 0.169 |
| K | 14.9 | | 15.1 | 0.586 | | 0.594 |
| L | 30.1 | | 30.3 | 1.185 | | 1.193 |
| M | 37.8 | | 38.2 | 1.488 | | 1.503 |
| N | 4 | | | 0.157 | | |
| O | 7.8 | | 8.2 | 0.307 | | 0.322 |



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